

BRCS4N10TA

Rev.A Jun.-2021

描述 / Descriptions

SOT-89 塑封封装 N 沟道 MOS 场效应管。

N- CHANNEL MOSFET in a SOT-89 Plastic Package.

特征 / Features

$V_{DS} (V) = 100V$

$I_D = 4A (V_{GS} = 10V)$

$R_{DS(ON)} < 115m\Omega (V_{GS} = 10V)$

$R_{DS(ON)} < 150m\Omega (V_{GS} = 4.5V)$

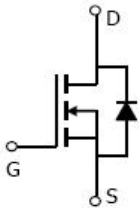
无卤产品。HF Product.

用途 / Applications

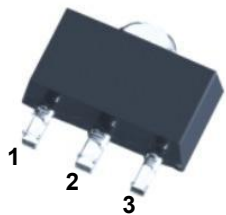
适用于作负载开关或脉宽调制应用。

This device is suitable for use as a load switch or in PWM applications.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN 1 : G

PIN 2 : D

PIN 3 : S

印章代码 / Marking

详见印章说明页。 See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DS}	100	V
Continuous Drain Current	I_D	4	A
Pulsed Drain Current	I_{DM}	16	A
Gate-Source Voltage	V_{GS}	± 20	V
Total Power Dissipation	P_D	2.0	W
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-55 to 150	°C
Maximum Junction-to-Ambient	$t \leq 10s$	$R_{\theta JA}$	62.5
Maximum Junction-to-Ambient	Steady-State		87
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	55.5

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V$ $V_{GS}=0V$			1	μA
		$V_{DS}=100V$ $V_{GS}=0V$ $T_J=55^\circ C$			5	μA
Gate-Body Leakage.	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.2	1.6	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)(1)}$	$V_{GS}=10V$ $I_D=1A$		107	115	$m\Omega$
	$R_{DS(on)(2)}$	$V_{GS}=4.5V$ $I_D=1A$		140	150	
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1A$			1.2	V

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1MHz$		190		pF
Output Capacitance	C_{oss}			155		
Reverse Transfer Capacitance	C_{rss}			28		
Gate resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$ $f=1MHz$		0.8		Ω
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V,$ $V_{DS}=50V,$ $I_D=4A$		3.8		nC
Total Gate Charge	$Q_{g(4.5V)}$			1.8		
Gate Source Charge	Q_{gs}			0.8		
Gate Drain Charge	Q_{gd}			0.8		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $R_L=25\Omega$ $V_{DS}=50V$ $R_{GEN}=3\Omega$		5		ns
Turn-On Rise Time	t_r			3		
Turn-Off Delay Time	$t_{d(off)}$			19		
Turn-Off Fall Time	t_f			3		

电参数曲线图 / Electrical Characteristic Curve

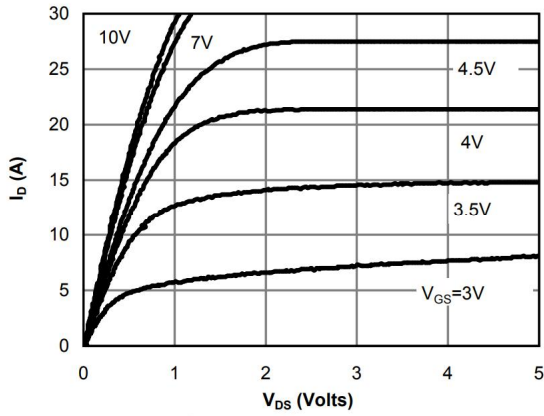


Fig 1: On-Region Characteristics

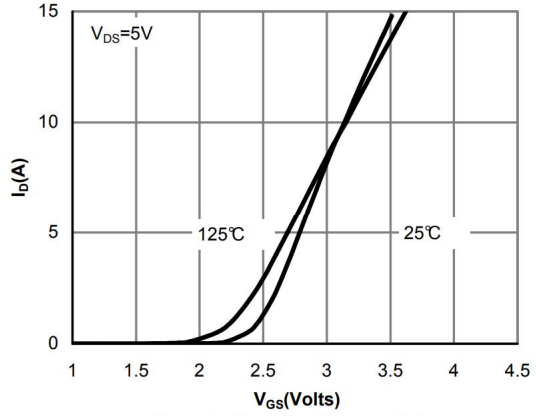


Figure 2: Transfer Characteristics

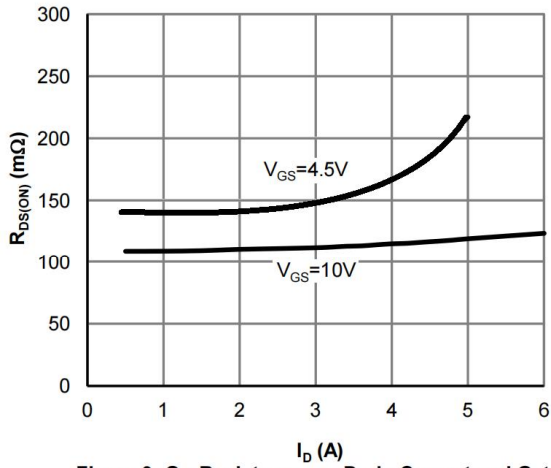


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

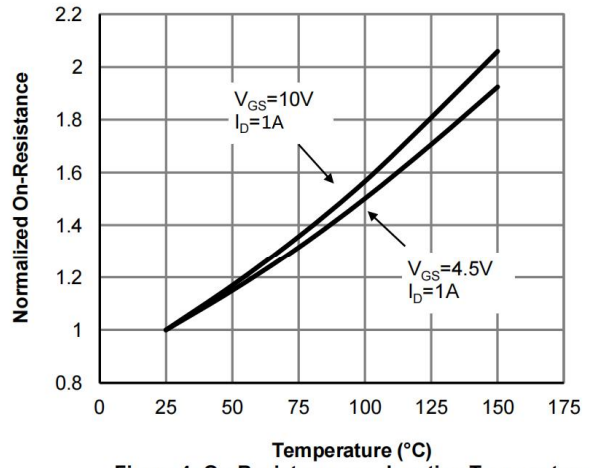


Figure 4: On-Resistance vs. Junction Temperature

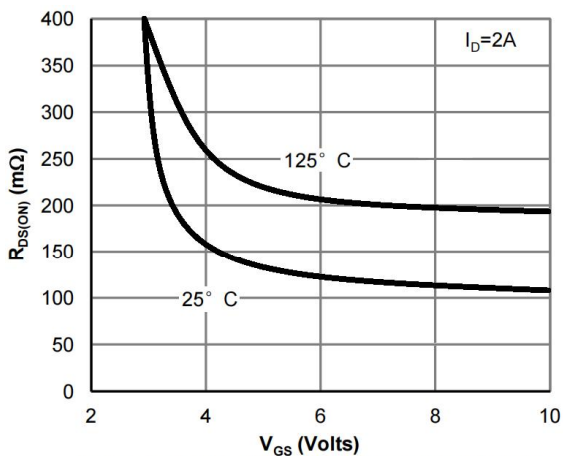


Figure 5: On-Resistance vs. Gate-Source Voltage

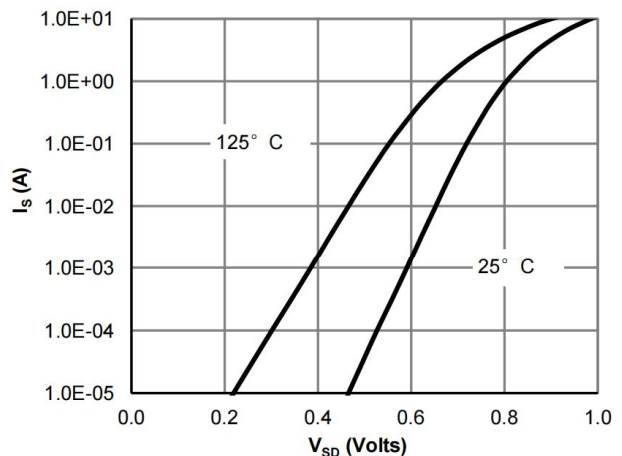


Figure 6: Body-Diode Characteristics

电参数曲线图 / Electrical Characteristic Curve

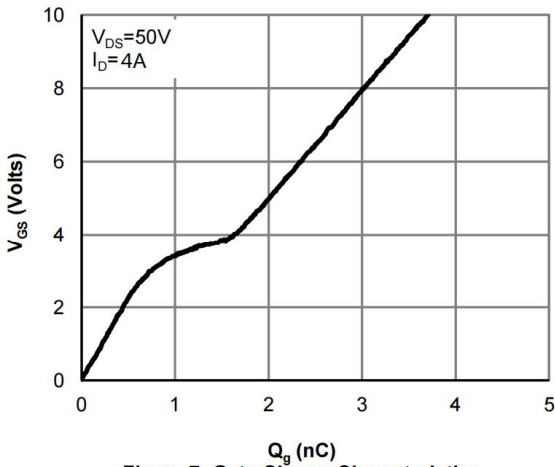


Figure 7: Gate-Charge Characteristics

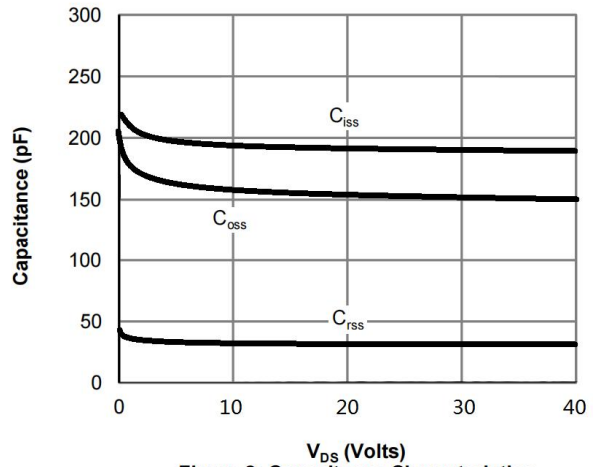


Figure 8: Capacitance Characteristics

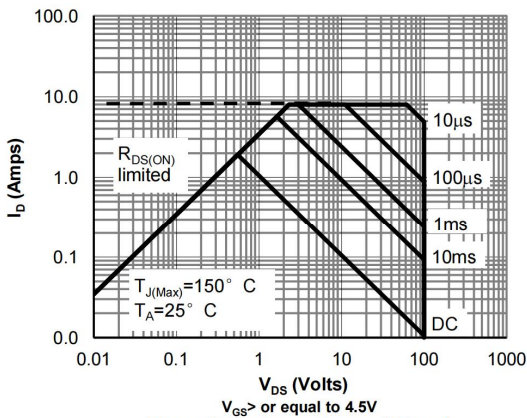


Figure 9: Maximum Forward Biased Safe Operating Area

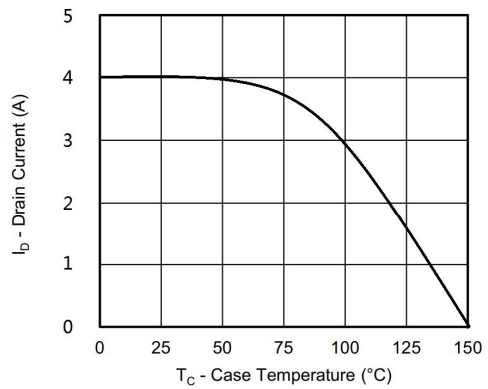


Figure 10: Maximum Continuous Drain Current vs Case Temperature

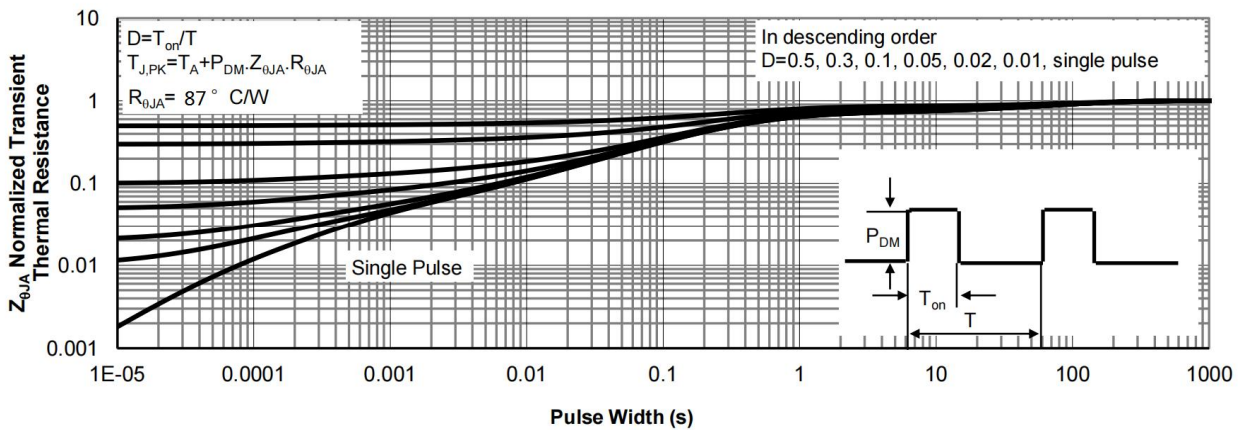
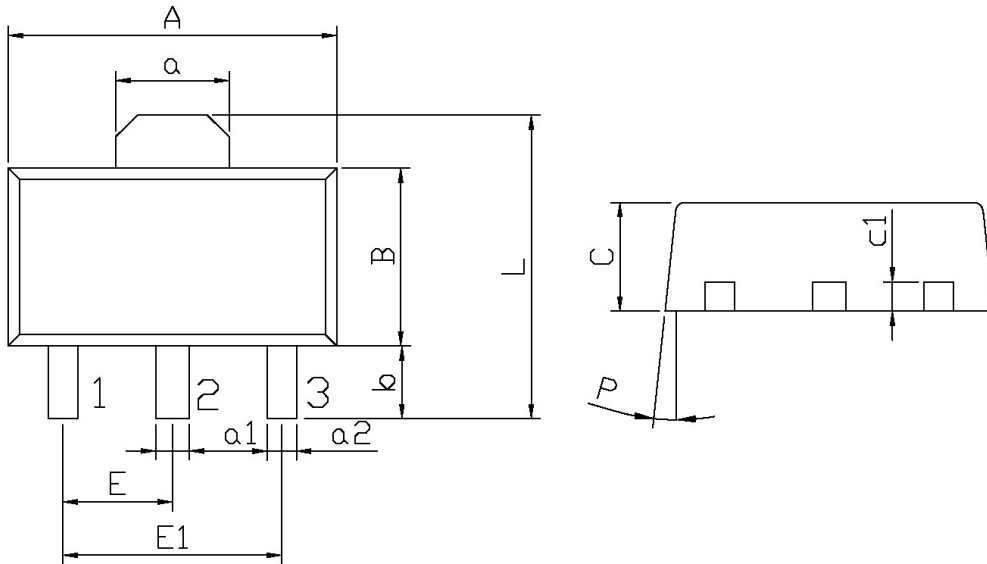


Figure 11: Normalized Maximum Transient Thermal Impedance

外形尺寸图 / Package Dimensions

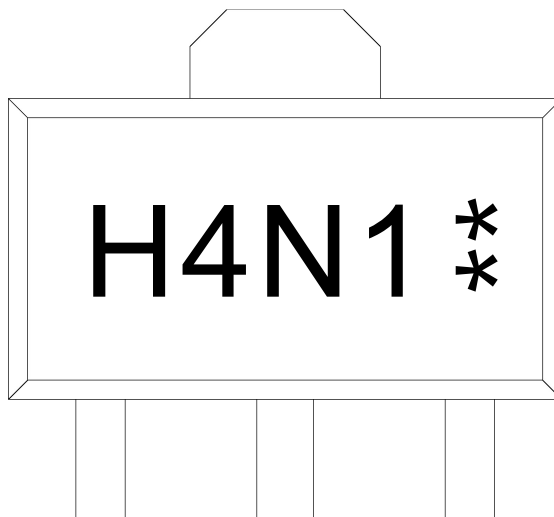
SOT-89

单位: mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	4.4	4.7	a1	0.36	0.56
B	2.35	2.65	a2	0.30	0.50
L	3.878	4.478	C	1.40	1.70
a	1.45	1.65	c1	0.35	0.50
E	1.40	1.60	P	6°	
E1	2.80	3.20			
b	0.80	1.20			

印章说明 / Marking Instructions



说明：

4N1： 为型号代码

H： 为公司代码

**： 为生产批号代码，随生产批号变化。

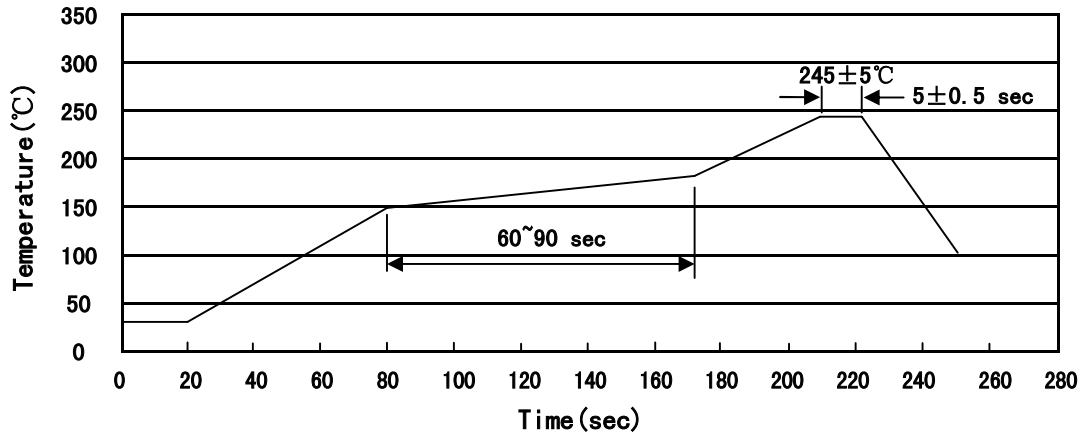
Note:

4N1: Product Type Code.

H: Company Code.

** : Lot No. Code, code change with Lot No.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150 ~ 180°C，时间 60 ~ 90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-89	1,000	7	7,000	6	42,000	7" ×12	180×120×180	390×358×205

使用说明 / Notices

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